P3A9606JK

Dual bidirectional I3C/I^{2}C-bus and SPI voltage-level translator

Rev. 1.0 — 10 May 2021 Product data sheet

1 General description

The P3A9606JK is a 2-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation for traditional I^{2}C-bus/SMBus applications, 12.5 MHz I3C-bus applications and also higher speed SPI applications (with two devices). It features two 1-bit input-output ports (An and Bn), one output enable input (OE) and two supply pins (V_{CCA} and V_{CCB}). V_{CCA} can be supplied at any voltage between 0.72 V and 1.98 V and V_{CCB} can be supplied at any voltage between 0.72 V and 1.98 V, making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V and 1.8 V). V_{CCA} must be ≤ V_{CCB} to ensure proper operation.

P3A9606JK can be used for both open drain as well as push-pull application which allows for level translation applications using I3C, I^{2}C and SPI protocols.

Pins An are referenced to V_{CCA} and pins Bn are referenced to V_{CCB}. The active HIGH OE pin is referenced to V_{CCA} and controllable by a signal in either V_{CCA} or V_{CCB} domain. A LOW level at pin OE causes the outputs to be in a high-impedance OFF-state. This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2 Features and benefits

- Wide supply voltage range:
  - V_{CCA}: 0.72 V to 1.98 V and V_{CCB}: 0.72 V to 1.98 V; $V_{CCA} \leq V_{CCB}$
- I_{OFF} circuitry provides partial Power-down mode operation
- Inputs accept voltages up to 1.98 V and are overvoltage tolerant to 1.98 V
- Provided voltage level translation for I3C, I^{2}C-bus, SMBus and SPI devices
- ESD protection:
  - HBM JESD22-A114E Class 2 exceeds 2000 V
  - CDM JESD22-C101E exceeds 1000 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Available in X2SON8 package
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3 Ordering information

Table 1. Ordering information

Type number	Topside marking	Package		
		Name	Description	Version
P3A9606JK	Tx [1]	X2SON8	super thin small outline package, no leads; 8 terminals; 0.35 mm pitch; 1.35 mm x 1.0 mm x 0.32 mm body	SOT2015-1

[1] "x" changes based on date code.

3.1 Ordering options

Table 2. Ordering options

Type number	Orderable part number	Package	Packing method	Minimum order quantity	Temperature
P3A9606JK	P3A9606JKZ	X2SON8	Reel 13” Q1/T1 *standard mark SMD with SSB [1]	20000	T_{amb} = -40 °C to +125 °C

[1] This packing method uses a Static Shielding Bag (SSB) solution. Material should be kept in the sealed bag between uses.

4 Block diagram

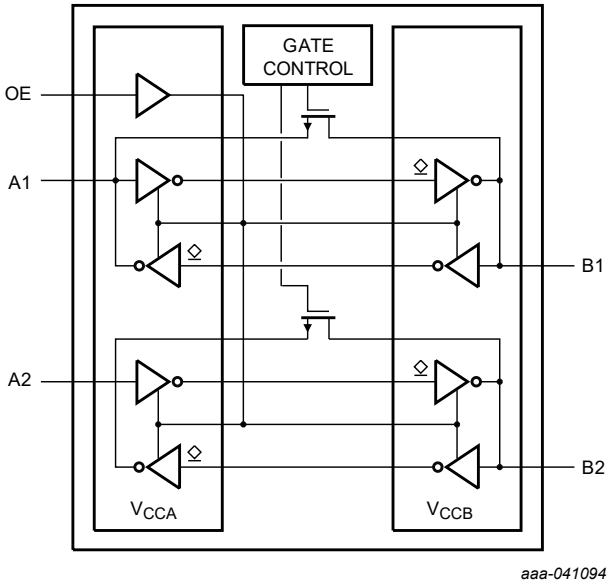
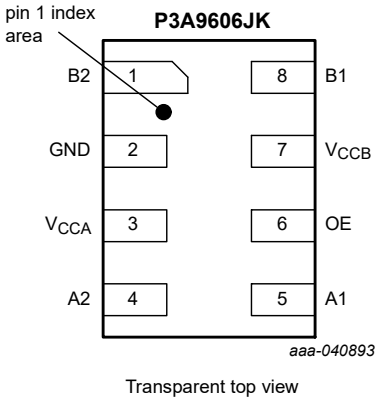


Figure 1. Block diagram

5 Pinning information

5.1 Pinning



Transparent top view

Figure 2. Pin configuration SOT2015-1

5.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B2, B1	1, 8	B port - data input or output (referenced to V_{CCB})
GND	2	ground (0 V)
V_{CCA}	3	supply voltage A
A2, A1	4, 5	A port - data input or output (referenced to V_{CCA})
OE	6	output enable input (active HIGH, referenced to V_{CCA}); signal can be from V_{CCA} or V_{CCB} domain
V_{CCB}	7	supply voltage B

6 Functional description

Table 4. Function table [1]

Supply voltage		Input	Input/output
V_{CCA}	V_{CCB}	OE [2]	
0.72 V to 1.98 V	0.72 V to 1.98 V	L	disconnected
0.72 V to 1.98 V	0.72 V to 1.98 V	H	A1 = B1; A2 = B2
GND [3]	GND [3]	X	disconnected

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care

[2] V_{IL} and V_{IH} are referenced to V_{CCA}. The OE can be controlled by an external device that is powered by either V_{CCA} or V_{CCB}. As V_{CCB} is required to be greater than V_{CCA}, the OE pin has been designed to withstand a voltage equal to V_{CCB} (up to 1.98 V per recommended functional voltage range).

[3] When either V_{CCA} or V_{CCB} is at GND level, the device goes into Power-down mode.

7 Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CCA}	supply voltage A	$V_{CCA} \leq V_{CCB}$		-0.5	2.5	V
V_{CCB}	supply voltage B	$V_{CCA} \leq V_{CCB}$		-0.5	2.5	V
V_I	input voltage	A port, B port and OE	[1]	-0.5	2.5	V
V_O	output voltage	Active mode	[1][2][3]	-0.5	V_{CCO} + 0.25	V
		Power-down or 3-state mode	[1]	-0.5	2.5	V
I_{IK}	input clamping current	V_I < 0 V		-50	-	mA
I_{OK}	output clamping current	V_O < 0 V		-50	-	mA
I_O	output current	V_O = 0 V to V_{CCO}	[2]	-	±50	mA
I_{CC}	supply current	$I_{CC(A)}$ or $I_{CC(B)}$		-	100	mA
I_{GND}	ground current			-100	-	mA
T_{stg}	storage temperature			-65	+150	°C
P_{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C		-	125	mW

[1] The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed.
[2] V_{CCO} is the supply voltage associated with the output.
[3] V_{CCO} + 0.25 V should not exceed 2.5 V.

8 Recommended operating conditions

Table 6. Recommended operating conditions[1]

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCA}	supply voltage A	$V_{CCA} \leq V_{CCB}$	0.72	1.98	V
V_{CCB}	supply voltage B	$V_{CCA} \leq V_{CCB}$	0.72	1.98	V
V_I	input voltage	A port, B port and OE	0	1.98	V
V_O	output voltage	Power-down or 3-state mode; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V			
		A port	0	1.98	V
		B port	0	1.98	V
T_{amb}	ambient temperature		-40	+125	°C
T_J	junction temperature[2]		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V	-	<5.3	ns/V

[1] The A and B sides of an unused I/O pair must be held in the same state, both at V_{CCI} or both at GND.
[2] The T_J limits shall be supported by proper thermal PCB design taking the power consumption and the thermal resistance as listed in Table 7 into account.

9 Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Value (typ)	Unit
$R_{th(j-a)}$	Thermal resistance from junction to ambient	X2SON8 package	114.9	°C/W
$\Psi_{(j-t)}$	Junction to top characterization	X2SON8 package	1.6	°C/W

10 Static characteristics

Table 8. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{OH}	HIGH-level output voltage	A port; V_{CCA} = 1.2 V; I_O = -20 µA		-	1.1	-	V
V_{OL}	LOW-level output voltage	A port; V_{CCA} = 1.2 V; I_O = 20 µA		-	0.09	-	V
I_I	input leakage current	OE input; V_I = 0 V or 1.98 V; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		-	-	±1	µA
I_{OZ}	OFF-state output current	A or B port; V_O = 0 V to V_{CCO}; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V	[1]	-	-	±1	µA
I_{OFF}	power-off leakage current	A port; V_I or V_O = 0 V to 1.98 V; V_{CCA} = 0 V; V_{CCB} = 0 V to 1.98 V		-	-	±1	µA
		B port; V_I or V_O = 0 V to 1.98 V; V_{CCB} = 0 V; V_{CCA} = 0 V to 1.98 V		-	-	±1	µA
I_{CC}	supply current	V_I = 0 V or V_{CCI}; I_O = 0 A	[2]				
		$I_{CC(A)}$; V_{CCA} = 0.72 V; V_{CCB} = 0.72 V to 1.98 V		-	0.05	-	µA
		$I_{CC(B)}$; V_{CCA} = 0.72 V; V_{CCB} = 0.72 V to 1.98 V		-	3.3	-	µA
		$I_{CC(A)}$ + $I_{CC(B)}$; V_{CCA} = 0.72 V; V_{CCB} = 0.72 V to 1.98 V		-	3.5	-	µA
C_I	input capacitance	OE input; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		-	1.0	-	pF
$C_{I/O}$	input/output capacitance	A port; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		-	4.0	-	pF
		B port; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		-	4.0	-	pF

[1] V_{CCO} is the supply voltage associated with the output.
[2] V_{CCI} is the supply voltage associated with the input.

Table 9. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).[1]

Symbol	Parameter	Conditions		-40 °C to +85 °C		-40 °C to +125 °C		Unit
				Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	A port or B port						
		V_{CCA} = 0.72 V to 0.9 V; V_{CCB} = 0.72 V to 0.9 V	[1]	V_{CCI} - 0.2	-	V_{CCI} - 0.2	-	V
		V_{CCA} = 0.9 V to 1.98 V; V_{CCB} = 0.9 V to 1.98 V	[1]	V_{CCI} - 0.4	-	V_{CCI} - 0.4	-	V
		OE input						
		V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		0.65V_{CCA}	-	0.65V_{CCA}	-	V
V_{IL}	LOW-level input voltage	A or B port						
		V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		-	0.3V_{CCA}	-	0.3V_{CCA}	V
		OE input						
		V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		-	0.3V_{CCA}	-	0.3V_{CCA}	V
V_{OH}	HIGH-level output voltage	I_O = -20 µA	[2]					
		A port; V_{CCA} = 0.72 V to 1.98 V		V_{CCO} - 0.4	-	V_{CCO} - 0.4	-	V
		B port; V_{CCB} = 0.72 V to 1.98 V		V_{CCO} - 0.4	-	V_{CCO} - 0.4	-	V
V_{OL}	LOW-level output voltage	I_O = 20 µA	[2]					
		A port; V_{CCA} = 0.72 V to 1.98 V		-	0.3	-	0.3	V
		B port; V_{CCB} = 0.72 V to 1.98 V		-	0.3	-	0.3	V
I_I	input leakage current	OE input; V_I = 0 V to 1.98 V; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		-	±2	-	±5	µA
I_{OZ}	OFF-state output current	A or B port; V_O = 0 V or V_{CCO}; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V	[2]	-	±2	-	±10	µA
I_{OFF}	power-off leakage current	A port; V_I or V_O = 0 V to 1.98 V; V_{CCA} = 0 V; V_{CCB} = 0 V to 1.98 V		-	±2	-	±10	µA
		B port; V_I or V_O = 0 V to 1.98 V; V_{CCB} = 0 V; V_{CCA} = 0 V to 1.98 V		-	±2	-	±10	µA
I_{CC}	supply current	V_I = 0 V or V_{CCI}; I_O = 0 A	[1]					
		$I_{CC(A)}$						
		OE = LOW; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		-	5	-	15	µA

Table 9. Static characteristics...*continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).[1]

Symbol	Parameter	Conditions	-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Max	Min	Max	
		OE = HIGH; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V	-	6	-	20	µA
		V_{CCA} = 1.98 V; V_{CCB} = 0 V	-	3.5	-	15	µA
		V_{CCA} = 0 V; V_{CCB} = 1.98 V	-	-2	-	-15	µA
		$I_{CC(B)}$					
		OE = LOW; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V	-	8	-	29	µA
		OE = HIGH; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V	-	11	-	36	µA
		V_{CCA} = 1.98 V; V_{CCB} = 0 V	-	-2	-	-15	µA
		V_{CCA} = 0 V; V_{CCB} = 1.98 V	-	6	-	20	µA
		$I_{CC(A)} + I_{CC(B)}$					
		OE = LOW; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V	-	16	-	56	µA

[1] V_{CCI} is the supply voltage associated with the input.
[2] V_{CCO} is the supply voltage associated with the output.

11 Dynamic characteristics

Table 10. Dynamic characteristics for temperature range -40 °C to +85 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol	Parameter	Conditions	V_{CCB}			
			1.2 V ± 10 %			
			Min	Typ	Max	Min
V_{CCA} = 0.8 V ± 10 %						
t_{pd}	propagation delay	A to B; C_L = 15 pF	2.1	5.6	7.7	1.7
		B to A; C_L = 15 pF	1.2	10.6	19.9	0.5
t_{en}	enable time	OE to A, B; C_L = 15 pF	16	125	150	16
t_{dis} [2]	disable time	OE to A; no external load [3]	10		25	10
		OE to B; no external load [3]	10		25	10
		OE to A; C_L = 15 pF			50	
		OE to B; C_L = 15 pF			50	
t_t	transition time	A port; C_L = 15 pF	2.1	8.5	17.5	1.5
		B port; C_L = 15 pF	1.1	4	5.8	0.7
$t_{sk(o)}$	output skew time	delta between channels [4]	0	0.2	0.4	0
t_W	pulse width	data inputs	37			37
f_{data}	data rate		0.064		26	0.064

[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{en} is the same as t_{PZL} and t_{PZH}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_t is the same as t_{THL} and t_{TLH}.
[2] Guaranteed by design.
[3] Delay between OE going LOW and when the outputs are actually disabled.
[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

Table 11. Dynamic characteristics for temperature range -40 °C to +85 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol	Parameter	Conditions	V_{CCB} 1.2 V ± 10 %			
			Min	Typ	Max	Min
V_{CCA} = 1.2 V ± 10 %						
t_{pd}	propagation delay	A to B; C_L = 15 pF	1.5	4.5	6.1	1.0
		B to A; C_L = 15 pF	1.1	3.9	5.3	0.6
t_{pdc}	propagation delay	A to B; C_L = 80 pF	NA	NA	NA	2.5
		B to A; C_L = 30 pF	NA	NA	NA	0.9
t_{en}	enable time	OE to A, B; C_L = 15 pF	10	50	100	10
t_{dis} [2]	disable time	OE to A; no external load [3]	10		25	10
		OE to B; no external load [3]	10		25	10
		OE to A; C_L = 15 pF			50	-
		OE to B; C_L = 15 pF			50	-
t_t	transition time	A port; C_L = 15 pF	0.8	2.6	3.5	0.6
		B port; C_L = 15 pF	1.1	3.6	5.1	0.6
t_{tc}	transition time	A port; C_L = 30 pF	NA	NA	NA	1.0
		B port; C_L = 80 pF	NA	NA	NA	2.5
$t_{sk(o)}$	output skew time	delta between channels [4]	0.0	0.1	0.2	0.0
t_W	pulse width	data inputs	15			13.5
f_{data}	data rate		0.064		52	0.064

[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{en} is the same as t_{PZL} and t_{PZH}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_t is the same as t_{THL} and t_{TLH}.
[2] Guaranteed by design.
[3] Delay between OE going LOW and when the outputs are actually disabled.
[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

Table 12. Dynamic characteristics for temperature range -40 °C to +85 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions	1.8
			Min	Typ
V_{CCA} = 1.8 V ± 10 %				
t_{pd}	propagation delay	A to B; C_L = 15 pF	1	2.5
		B to A; C_L = 15 pF	0.7	2.3
t_{en}	enable time	OE to A, B; C_L = 15 pF	8	25
t_{dis} [2]	disable time	OE to A; no external load [3]	10	
		OE to B; no external load [3]	10	
		OE to A; C_L = 15 pF		
		OE to B; C_L = 15 pF		
t_t	transition time	A port; C_L = 15 pF	0.5	1.2
		B port; C_L = 15 pF	0.7	1.7
$t_{sk(o)}$	output skew time	delta between channels [4]	0	0.1
t_W	pulse width	data inputs	13.5	
f_{data}	data rate		0.064	

[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{en} is the same as t_{PZL} and t_{PZH}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_t is the same as t_{THL} and t_{TLH}.
[2] Guaranteed by design.
[3] Delay between OE going LOW and when the outputs are actually disabled.
[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol	Parameter	Conditions	V_{CCB}			V_{CCB}
			1.2 V ± 10 %			1.8 V ± 10 %
			Min	Typ	Max	Min
V_{CCA} = 0.8 V ± 10 %						
t_{pd}	propagation delay	A to B; C_L = 15 pF	2.1	5.6	7.7	1.7

Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C [1]*...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol	Parameter	Conditions	V_{CCB} 1.2 V ± 10 %			V_{CCB} 1.8 V ± 10 %
			Min	Typ	Max	Min
		B to A; C_L = 15 pF	1.2	10.6	19.9	0.5
t_{en}	enable time	OE to A, B; C_L = 15 pF	16	125	150	16
t_{dis} [2]	disable time	OE to A; no external load [3]	10		25	10
		OE to B; no external load [3]	10		25	10
		OE to A; C_L = 15 pF			50	
		OE to B; C_L = 15 pF			50	
t_t	transition time	A port; C_L = 15 pF	2.1	8.5	17.5	1.5
		B port; C_L = 15 pF	1.1	4	5.8	0.7
$t_{sk(o)}$	output skew time	delta between channels [4]	0	0.2	0.4	0
t_W	pulse width	data inputs	37			37
f_{data}	data rate		0.064		26	0.064

[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{en} is the same as t_{PZL} and t_{PZH}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_t is the same as t_{THL} and t_{TLH}.
[2] Guaranteed by design.
[3] Delay between OE going LOW and when the outputs are actually disabled.
[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

Table 14. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions	V_{CCB} 1.2 V ± 10 %			V_{CCB} 1.8 V ±
			Min	Typ	Max	Min
V_{CCA} = 1.2 V ± 10 %						
t_{pd}	propagation delay	A to B; C_L = 15 pF	1.5	4.5	6.2	1.0
		B to A; C_L = 15 pF	1.1	3.9	5.4	0.6
t_{pdc}	propagation delay	A to B; C_L = 80 pF	NA	NA	NA	2.5

Table 14. Dynamic characteristics for temperature range -40 °C to +125 °C [1]*...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions	V_{CCB} 1.2 V ± 10 %			V_{CCB} 1.8 V ±
			Min	Typ	Max	Min
		B to A; C_L = 30 pF	NA	NA	NA	0.9
t_{en}	enable time	OE to A, B; C_L = 15 pF	10	50	100	10
t_{dis} [2]	disable time	OE to A; no external load [3]	10		25	10
		OE to B; no external load [3]	10		25	10
		OE to A; C_L = 15 pF			50	-
		OE to B; C_L = 15 pF			50	-
t_t	transition time	A port; C_L = 15 pF	0.8	2.6	3.5	0.6
		B port; C_L = 15 pF	1.1	3.6	5.1	0.6
t_{tc}	transition time	A port; C_L = 30 pF	NA	NA	NA	1.0
		B port; C_L = 80 pF	NA	NA	NA	2.5
$t_{sk(o)}$	output skew time	delta between channels [4]	0	0.1	0.2	0
t_W	pulse width	data inputs	15			13.5
f_{data}	data rate		0.064		52	0.064

[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{en} is the same as t_{PZL} and t_{PZH}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_t is the same as t_{THL} and t_{TLH}.
[2] Guaranteed by design.
[3] Delay between OE going LOW and when the outputs are actually disabled.
[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

Table 15. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions	V_C 1.8 V	
			Min	Typ
V_{CCA} = 1.8 V ± 10 %				
t_{pd}	propagation delay	A to B; C_L = 15 pF	1	2.5

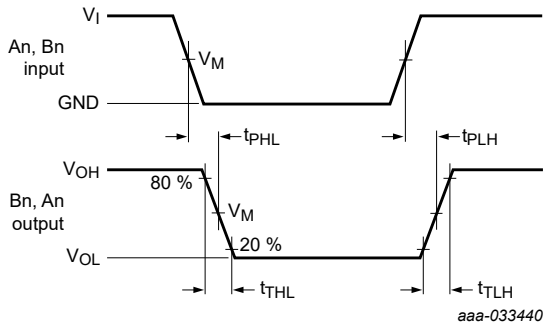
Table 15. Dynamic characteristics for temperature range -40 °C to +125 °C [1]*...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions	V_C 1.8 V	
			Min	Typ
		B to A; C_L = 15 pF	0.7	2.3
t_{en}	enable time	OE to A, B; C_L = 15 pF	8	25
t_{dis} [2]	disable time	OE to A; no external load [3]	10	
		OE to B; no external load [3]	10	
		OE to A; C_L = 15 pF		
		OE to B; C_L = 15 pF		
t_t	transition time	A port; C_L = 15 pF	0.5	1.2
		B port; C_L = 15 pF	0.7	1.7
$t_{sk(o)}$	output skew time	delta between channels [4]	0	0.1
t_W	pulse width	data inputs	13.5	
f_{data}	data rate		0.064	

[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{en} is the same as t_{PZL} and t_{PZH}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_t is the same as t_{THL} and t_{TLH}.
[2] Guaranteed by design.
[3] Delay between OE going LOW and when the outputs are actually disabled.
[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

12 Waveforms



Measurement points are given in Table 16.

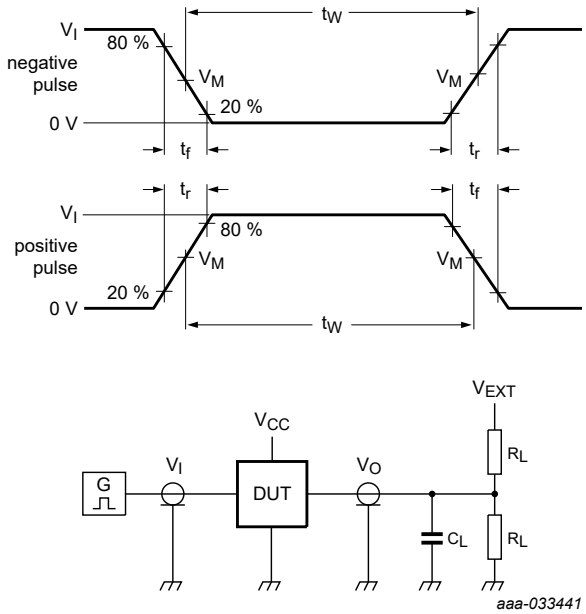
V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Figure 3. Data input (An, Bn) to data output (Bn, An) propagation delay times

Table 16. Measurement points

V_{CCI} is the supply voltage associated with the input and V_{CCO} is the supply voltage associated with the output.

Supply voltage	Input	Output		
V_{CCO}	V_M	V_M	V_X	V_Y
0.8 V ± 10 %	$0.5V_{CCI}$	$0.5V_{CCO}$	V_{OL} + 0.08 V	V_{OH} - 0.08 V
1.2 V ± 10 %	$0.5V_{CCI}$	$0.5V_{CCO}$	V_{OL} + 0.12 V	V_{OH} - 0.12 V
1.8 V ± 10 %	$0.5V_{CCI}$	$0.5V_{CCO}$	V_{OL} + 0.18 V	V_{OH} - 0.18 V



Test data is given in Table 17.

All input pulses are supplied by generators having the following characteristics: PRR ≤ 26 MHz; Z_O = 50 Ω; dV/dt ≥ 1.0 V/ns.

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

V_{EXT} = External voltage for measuring switching times.

Figure 4. Test circuit for measuring switching times

Table 17. Test data

Supply voltage		Input		Load		V_{EXT}		
V_{CCA}	V_{CCB}	V_I [1]	Δt/ΔV	C_L	R_L [2]	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ} [3]
0.72 V to 1.98 V	0.72 V to 1.98 V	V_{CCI}	≤ 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	$2V_{CCO}$

[1] V_{CCI} is the supply voltage associated with the input.

[2] For measuring data rate, pulse width, propagation delay and output rise and fall measurements, R_L = 1 MΩ; for measuring enable and disable times, R_L = 50 kΩ.

[3] V_{CCO} is the supply voltage associated with the output.

13 Application information

13.1 Applications

Voltage level-translation applications. The P3A9606JK can be used to interface between devices or systems operating at different supply voltages. See Figure 5, Figure 6, Figure 7 and Figure 8 for a typical operating circuit using the P3A9606JK.

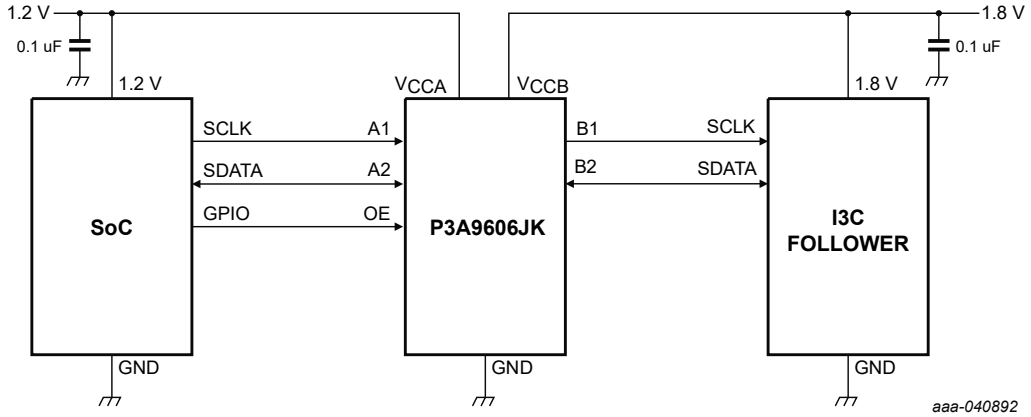


Figure 5. I3C application block diagram

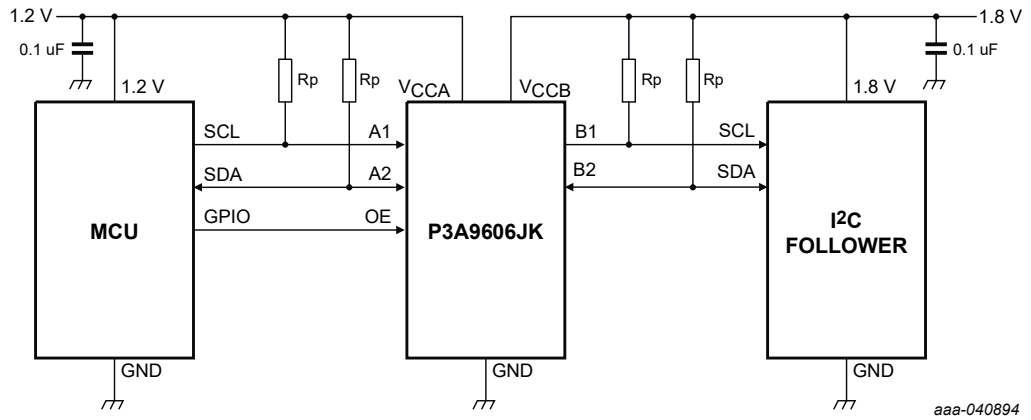


Figure 6. I²C application block diagram

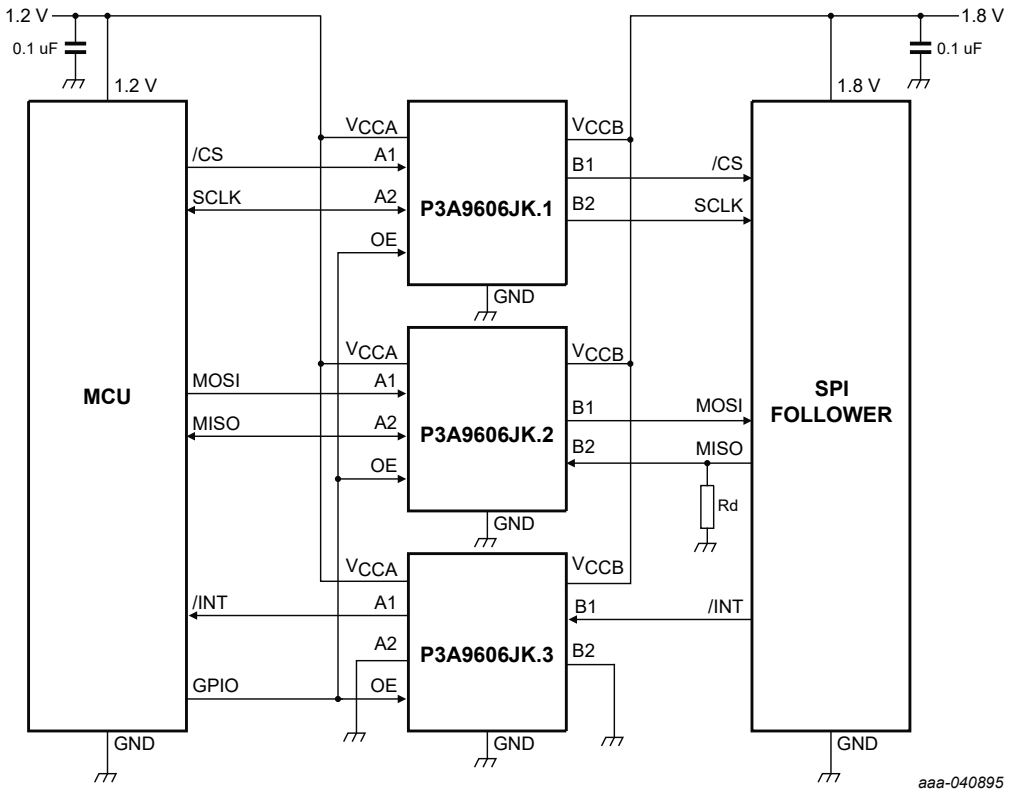


Figure 7. SPI application block diagram

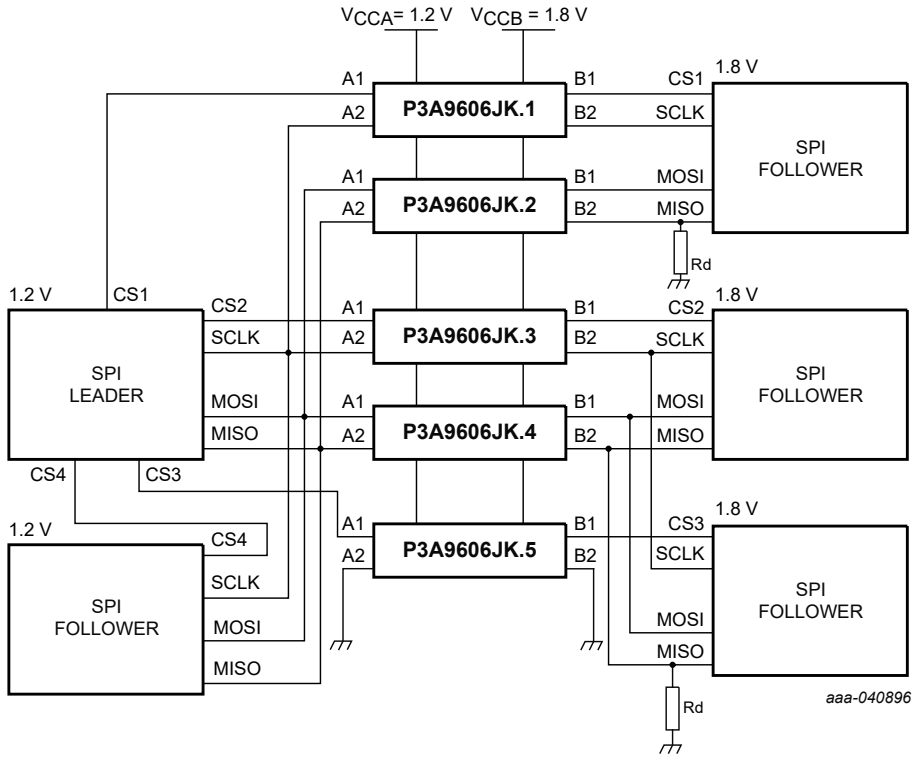


Figure 8. Complex SPI block diagram

13.2 Architecture

The architecture uses edge-rate accelerator circuitry (for both the high-to-low and low-to-high), N-Channel Pass gate transistor and a pull-up resistor (to provide DC-bias and drive capabilities) to meet these requirements. The design is directionless and does not need direction control signal. The implementation supports both low speed Open-drain operation as well as high speed push-pull operation. The N-Channel Pass device will be on only during Low input cycle and will be off during High input cycle.

13.3 Input driver requirements

The continuous DC- current sinking or sourcing capability is determined by the external system-level; open-drain or push-pull drivers that are interfaced to the P3A9606JK IO pins.

The high bandwidth of these IO circuits used to facilitate this fast change from an input to an output and an output to an input, they have a modest sourcing capability of hundreds of micro-amperes, as determined by the pull-up resistor.

The fall time of a signal depends on the edge-rate and output impedance of the external driving the P3A9606JK data IOs, as well as the capacitive loading at the data lines.

13.4 Power-up and power-down

During operation, ensure that $V_{CCA} \leq V_{CCB}$ at all times. The sequencing of each power supply will not damage the device during the power up operation, so either power supply can be ramped up first. There is no special power-up sequencing required. The

P3A9606JK includes circuitry that disables all output ports and puts the device into a power-down mode when either V_{CCA} or V_{CCB} is switched off.

13.5 Enable and disable

An output enable input (OE) is used to disable the device. Setting OE = LOW causes all I/Os to assume the high-impedance OFF-state. The disable time (t_{dis} with no external load) indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time (t_{en}) indicates the amount of time the user must allow for one one-shot circuitry to become operational after OE is taken HIGH. To ensure the high-impedance OFF-state during power-up or power-down, pin OE should be tied to GND, OE pin should not be left floating in any condition.

OE V_{IL} and V_{IH} are referenced to V_{CCA}. The OE can be controlled by an external device that is powered by either V_{CCA} or V_{CCB}. As V_{CCB} is required to be greater than V_{CCA}, the OE pin has been designed to withstand a voltage equal to V_{CCB} (up to 1.98 V per recommended functional voltage range).

13.6 Layout guidelines

To ensure reliability of the device, the following common printed-circuit board layout guidelines are recommended:

- Bypass capacitors should be used on power supplies and should be placed as close as possible to V_{CCA}, V_{CCB}, and GND pins.
- Short trace lengths should be used to avoid excessive loading.
- PCB signal trace-lengths must be kept short enough so that the round-trip delay of any reflection is less than the one-shot duration, approximately 8 ns, ensuring that any reflection encounters low impedance at the source driver.

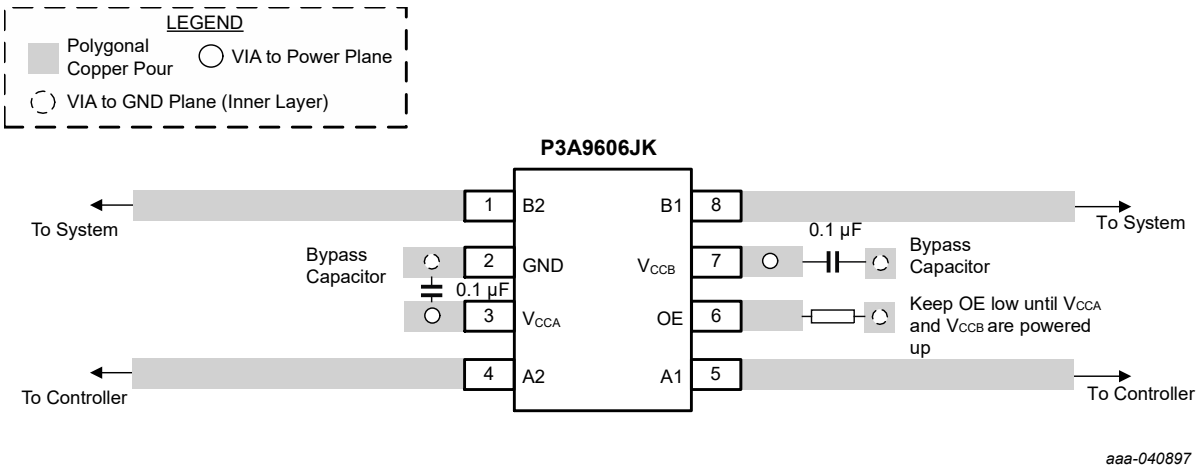


Figure 9. P3A9606JK layout example

14 Package outline

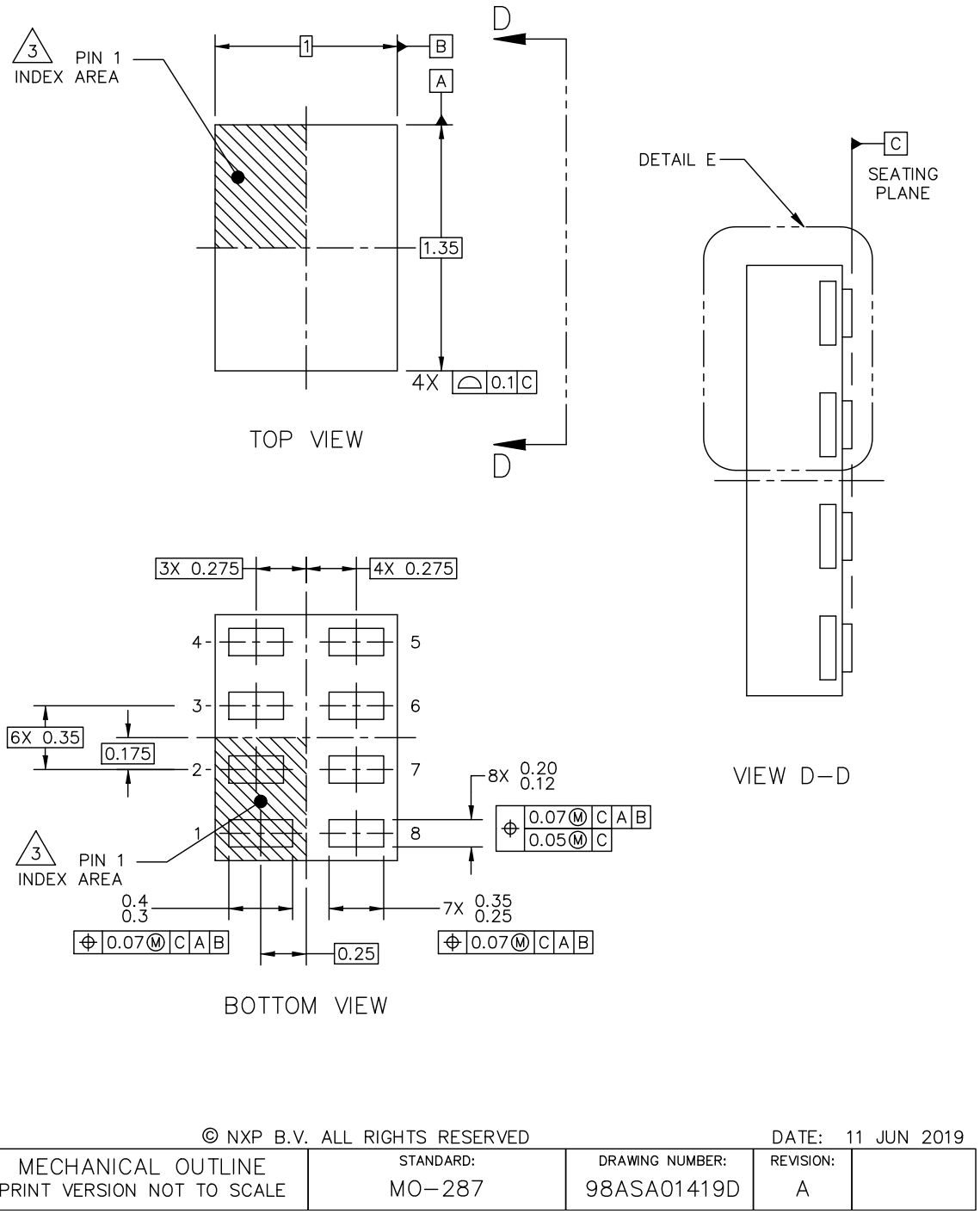


Figure 10. Package outline SOT2015-1

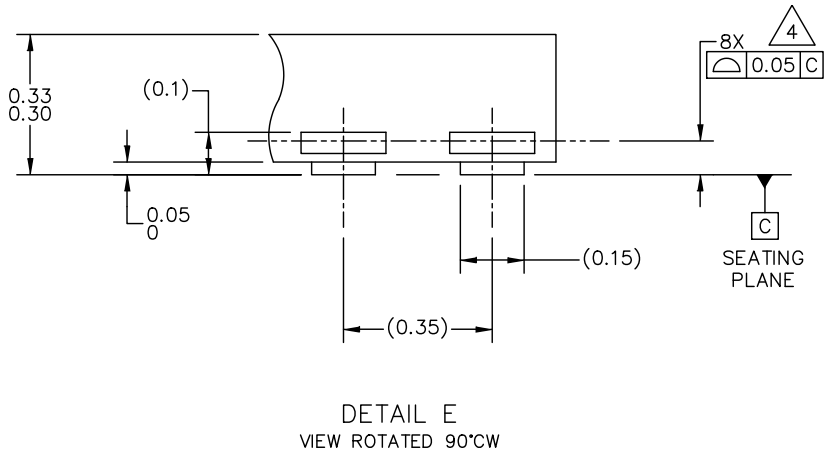


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Figure 11. Package outline SOT2015-1

15 Soldering

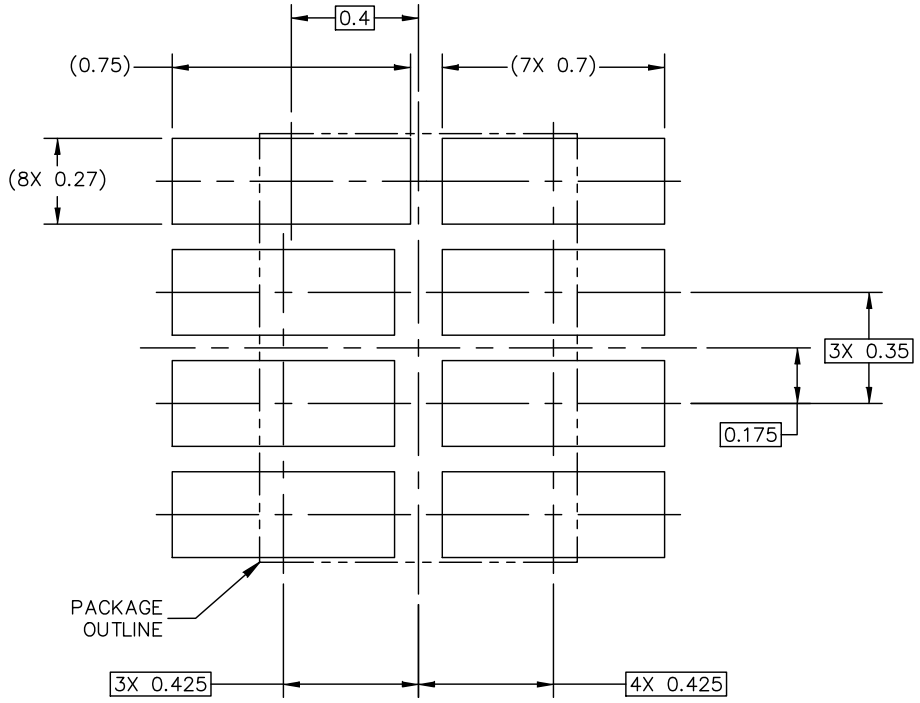

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Figure 12. Soldering footprint for SOT2015-1

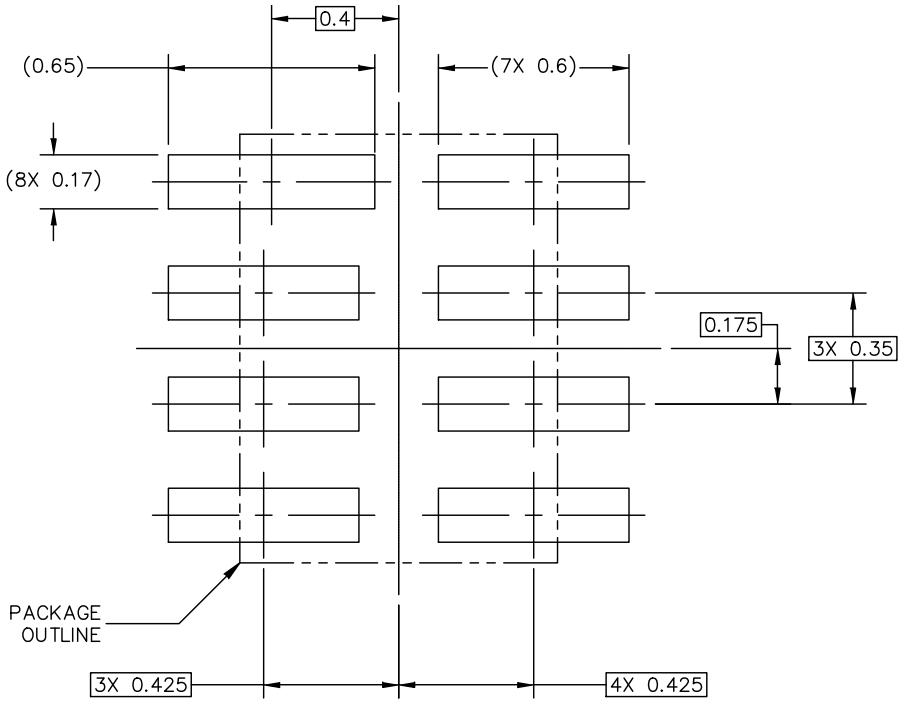

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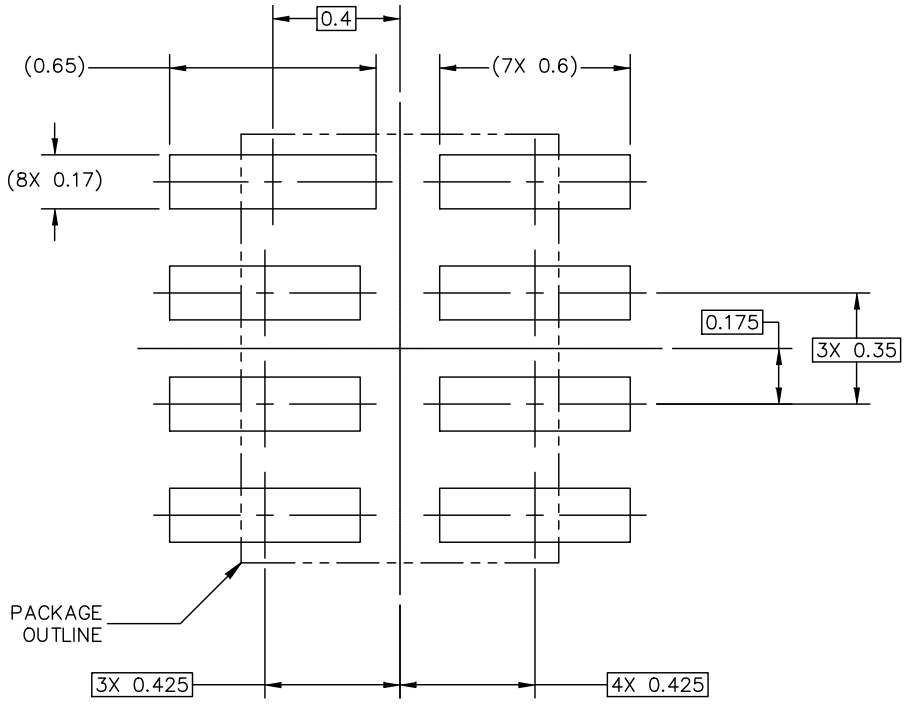
Figure 13. Soldering footprint for SOT2015-1



RECOMMENDED STENCIL THICKNESS 0.1

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Figure 14. Soldering footprint for SOT2015-1

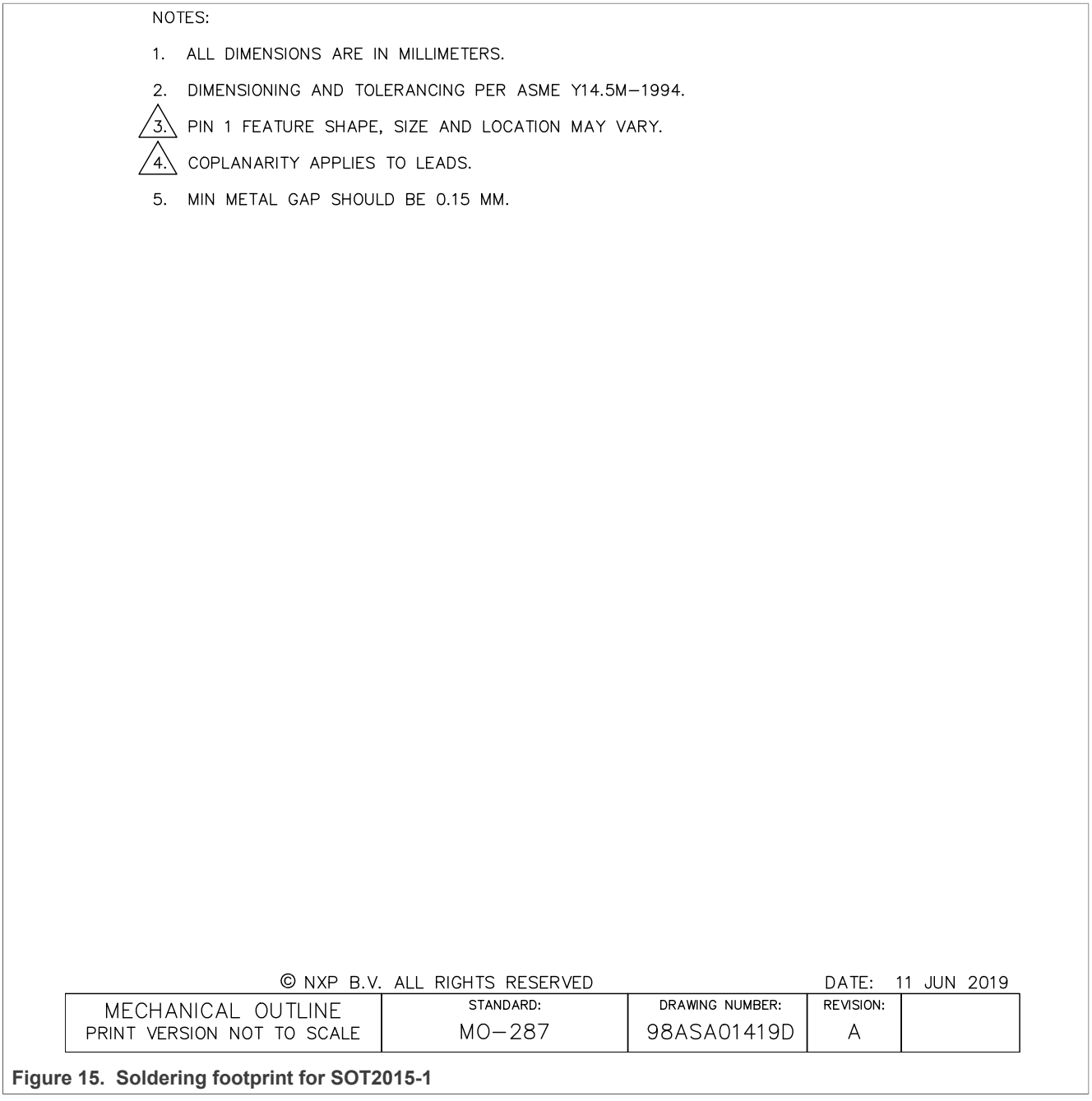

Figure 15. Soldering footprint for SOT2015-1

16 Abbreviations

Table 18. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
NMOS	N-type Metal Oxide Semiconductor
PMOS	P-type Metal Oxide Semiconductor
PRR	Pulse Repetition Rate

17 Revision history

Table 19. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
P3A9606JK v.1.0	20210510	Product data sheet	-	-

18 Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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